MOSFETs Silicon N-channel MOS (U-MOSVII-H)

# TPH2900ENH

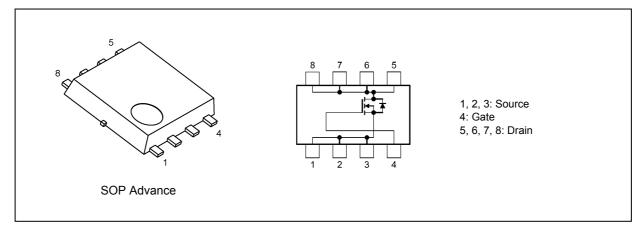
#### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 8.2 \text{ nC}$  (typ.)
- (3) Low drain-source on-resistance:  $R_{DS(ON)} = 24 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (4) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 200 \ V)$
- (5) Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1.0 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characterist                  | tics                     |                    | Symbol           | Rating     | Unit |
|-------------------------------|--------------------------|--------------------|------------------|------------|------|
| Drain-source voltage          |                          |                    | V <sub>DSS</sub> | 200        | V    |
| Gate-source voltage           |                          |                    | V <sub>GSS</sub> | ±20        |      |
| Drain current (DC)            | (Silicon limit)          | (Note 1), (Note 2) | Ι <sub>D</sub>   | 36         | A    |
| Drain current (DC)            | (Continuous)             | (Note 1)           | Ι <sub>D</sub>   | 33         |      |
| Drain current (pulsed)        | (t = 1 ms)               | (Note 1)           | I <sub>DP</sub>  | 102        |      |
| Power dissipation             | (T <sub>c</sub> = 25 °C) |                    | PD               | 78         | w    |
| Power dissipation             | (t = 10 s)               | (Note 3)           | PD               | 2.8        |      |
| Power dissipation             | (t = 10 s)               | (Note 4)           | PD               | 1.6        |      |
| Single-pulse avalanche energy |                          | (Note 5)           | E <sub>AS</sub>  | 176        | mJ   |
| Avalanche current             |                          |                    | I <sub>AR</sub>  | 33         | A    |
| Channel temperature           |                          |                    | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature           |                          |                    | T <sub>stg</sub> | -55 to 150 |      |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

| Characteristics                       | Symbol                   | Max      | Unit                  |      |      |
|---------------------------------------|--------------------------|----------|-----------------------|------|------|
| Channel-to-case thermal resistance    | (T <sub>c</sub> = 25 °C) |          | R <sub>th(ch-c)</sub> | 1.60 | °C/W |
| Channel-to-ambient thermal resistance | (t = 10 s)               | (Note 3) | R <sub>th(ch-a)</sub> | 44.6 |      |
| Channel-to-ambient thermal resistance | (t = 10 s)               | (Note 4) | R <sub>th(ch-a)</sub> | 78.1 |      |

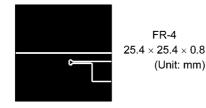
Note 1: Ensure that the channel temperature does not exceed 150 °C.

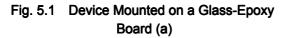
Note 2: Limited by silicon chip capability.

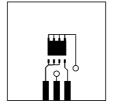
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V\_DD = 60 V, T\_ch = 25 °C (initial), L = 250  $\mu H, I_{AR}$  = 33 A







 $\begin{array}{c} \text{FR-4} \\ \text{25.4} \times \text{25.4} \times \text{0.8} \\ \text{(Unit: mm)} \end{array}$ 

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

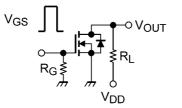
#### 6. Electrical Characteristics

#### 6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                  | Min | Тур. | Max  | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS}$ = ±20 V, $V_{DS}$ = 0 V                | _   | _    | ±0.1 | μA   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V  | _   |      | 10   |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V   | 200 |      | _    | V    |
|                                | V <sub>(BR)DSX</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V | 140 | _    | _    |      |
| Gate threshold voltage         | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA | 2.0 |      | 4.0  |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16.5 A | _   | 24   | 29   | mΩ   |

#### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition  | Min | Тур. | Max  | Unit |
|--------------------------------|------------------|---|-----|------|------|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 1700 | 2200 | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> |   | —   | 7.0  | 50   |      |
| Output capacitance             | C <sub>oss</sub> |   | _   | 180  | —    |      |
| Gate resistance                | rg               | —   | _   | 4.0  | 6.0  | Ω    |
| Switching time (rise time)     | t <sub>r</sub>   | See Fig. 6.2.1  |     | 8.0  | _    | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |   |     | 20   | _    |      |
| Switching time (fall time)     | t <sub>f</sub>   |   |     | 12   | _    |      |
| Switching time (turn-off time) | t <sub>off</sub> |   | _   | 36   | _    |      |



$$\begin{split} V_{DD} &\approx 100 \text{ V} \\ V_{GS} &= 0 \text{ V}/10 \text{ V} \\ I_D &= 16.5 \text{ A} \\ R_L &= 6.06 \Omega \\ R_G &= 4.7 \Omega \\ \text{Duty} &\leq 1 \ \%, \ t_w &= 10 \ \mu\text{s} \end{split}$$

Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

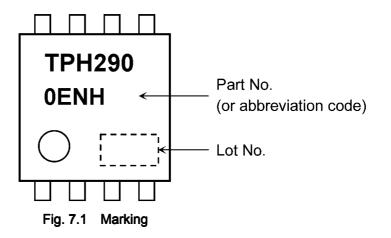
| Characteristics                                 | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD} \approx 100 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 33 \text{ A}$ | _   | 22   | —   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |   | _   | 9.0  | _   | nC   |
| Gate-drain charge                               | Q <sub>gd</sub>  | ]   | _   | 4.4  | _   |      |
| Gate switch charge                              | Q <sub>SW</sub>  |   |     | 8.2  |     |      |

#### 6.4. Source-Drain Characteristics (Ta = 25 °C unless otherwise specified)

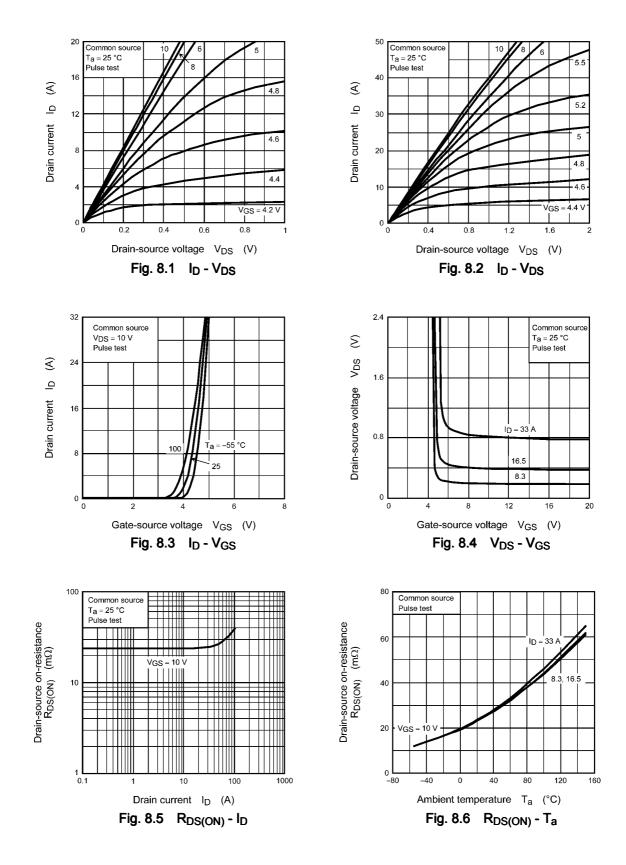
| Characteristics                |          | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|--------------------------------|----------|------------------|---|-----|------|------|------|
| Reverse drain current (pulsed) | (Note 6) | I <sub>DRP</sub> | —   | _   | _    | 102  | А    |
| Diode forward voltage          |          | $V_{DSF}$        | I <sub>DR</sub> = 33 A, V <sub>GS</sub> = 0 V | _   | _    | -1.2 | V    |

Note 6: Ensure that the channel temperature does not exceed 150 °C.

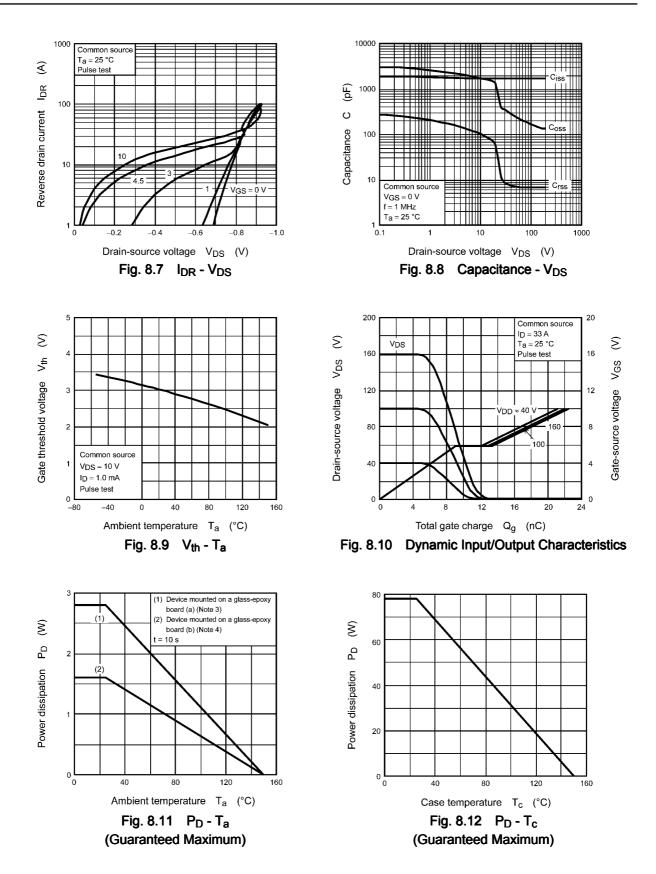
#### 7. Marking



#### 8. Characteristics Curves (Note)



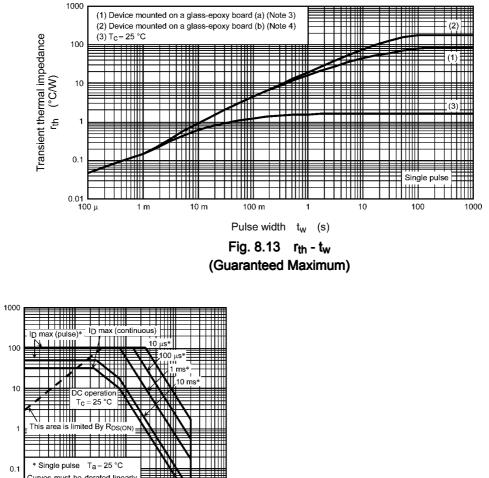


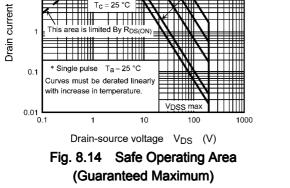




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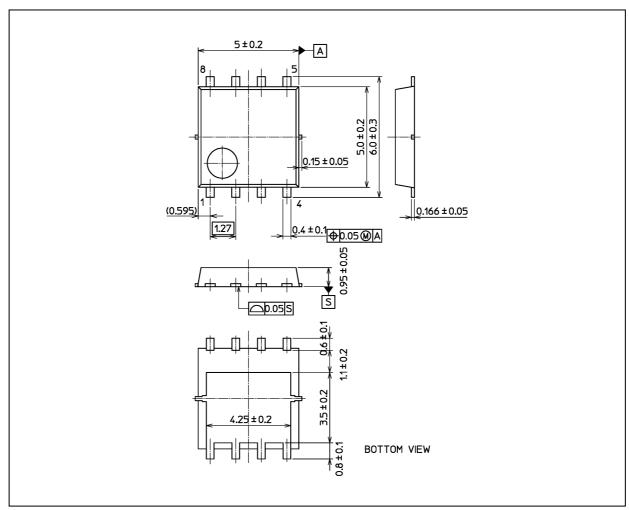


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### TPH2900ENH

#### Package Dimensions

Unit: mm



Weight: 0.087 g (typ.)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

Package Name(s)

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